

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S6	2	JP-01119037-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/26 15:44
S12	1	TW-421841-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/26 15:45
S13	1	TW-373282-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/26 15:45
S14	103	BRUCE-MICHAEL\$.in. BRUCE-VICTORIA\$.in. GILFEATHER-GLEN\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:21
S15	44	(BRUCE-MICHAEL\$.in. BRUCE-VICTORIA\$.in. GILFEATHER-GLEN\$.in.) and imag\$3 and remov\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:24
S16	127	(inspect\$4 or fault\$3 or defect\$3 or analys\$6 or analyz\$6) with (imag\$3 or electron adj (microscop\$2) or SEM or camera or CCD or video) with (remov\$3) near (substrate or layer or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit or die or dice)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:25
S17	24	382/141-151.ccls. and (remov\$3 or FIB or (ion or electron or e) near beam or etch\$3 or CMP or (mechanical\$2 near polish\$3) or cross adj section\$3) with (layer or substrate or wafer or die or dice or semiconductor or semi adj conductor) with (simultaneous\$2 or concurrent\$2 or "same" adj time or "in" adj process)	US-PGPUB; USPAT	OR	ON	2005/01/12 12:33
S18	118	((three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit) with (simultaneous\$2 or concurrent\$2 or "same" adj time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:38
S19	148	(imag\$3 or electron adj (microscop\$2) or SEM or camera or CCD or video) with (remov\$3 or FIB or ion near beam or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit) with (simultaneous\$2 or concurrent\$2 or "same" adj time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:44
S20	29	(inspect\$4 or fault\$3 or defect\$3 or analys\$6 or analyz\$6) same (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit) same (imag\$3 or electron adj (microscop\$2) or SEM or camera or CCD or video) with (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (simultaneous\$2 or concurrent\$2 or "same" adj time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 12:55

S21	40	(inspect\$4 or fault\$3 or defect\$3 or analys\$6 or analyz\$6) near (locat\$3 or caus\$3 or localiz\$6) same (imag\$3 or electron adj (microscop\$2) or SEM or camera or CCD or video or (three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or CMP or mechanical\$2 near polish\$3 or cross adj section\$3 or slic\$3 or dicing or cut or cutting or cleav\$3) near (substrate or layer or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit or die or dice\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 15:42
S22	5140	(inspect\$5 or fault\$3 or defect\$3 or analys\$6 or analyz\$6 or failure) same (imag\$3 or electron adj microscope or SEM or camera or CCD or video or (three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or CMP or mechanical\$2 near polish\$3 or cross adj section\$3 or slic\$3 or dicing or cut or cutting or cleav\$3) with (substrate or layer or semiconductor or semi adj conductor or IC or integrated adj circuit or die or dice\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:59
S25	206	(fault\$3 or defect\$3 or failure) with (imag\$3 or electron adj microscope or SEM or camera or CCD or video or (three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or CMP or mechanical\$2 near polish\$3 or cross adj section\$3 or slic\$3 or dicing or cut or cutting or cleav\$3) near (substrate or layer or semiconductor or semi adj conductor or IC or integrated adj circuit or die or dice\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 17:23
S26	2	JP-04174531-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 17:23
S28	2791	(SEM.u/c. or electron near microscope) with (stor\$3 or memory or record\$3 or sav\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:00
S29	507	(SEM.u/c. or electron near microscope) with (imag\$3 or picture) near (stor\$3 or memory or record\$3 or sav\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:11
S30	26	382/141-151.ccls. and (remov\$3 or FIB or (ion or electron or e) near beam or etch\$3 or CMP or (mechanical\$2 near polish\$3) or cross adj section\$3) with (layer or substrate or wafer or die or dice or semiconductor or semi adj conductor) with (simultaneous\$2 or concurrent\$2 or "same" adj time or "in" adj process)	US-PGPUB; USPAT	OR	ON	2005/08/02 14:42
S31	137	((three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit) with (simultaneous\$2 or concurrent\$2 or "same" adj time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:11
S32	9244	((three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:11
S33	2339	((three or "3") adj dimension\$4 or "3" adj D or 3D) same (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit) and image	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:12
S34	73	((three or "3") adj dimension\$4 or "3" adj D or 3D) near image\$2 same (remov\$3 or FIB or ion near beam or etch\$3 or CMP or mechanical\$2 near polish\$3 or cross adj section\$3) with (substrate or wafer or semiconductor or semi adj conductor or IC or integrated adj circuit)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:19

S35	30	three near dimension\$4 near image near edit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 14:25
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